			<u>H'1</u>
Notice of Allowability	Application No.	Applicant(s)	
	10/720,738 Examiner	SUGI ET AL.	
	Steven H. Rao	2814	
The MAILING DATE of this communication appeal All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIOF the Office or upon petition by the applicant. See 37 CFR 1.313	ears on the cover sheet with the co (OR REMAINS) CLOSED in this ap or other appropriate communication IGHTS. This application is subject to	correspondence addroplication. If not include n will be mailed in due	ed course. <b>THIS</b>
1. This communication is responsive to 3/16/05.			
2. A The allowed claim(s) is/are 1,3-8,13-15,17,21 and 23-29.			
3. $\boxtimes$ The drawings filed on <u>16 March 2005</u> are accepted by the	Examiner.		
4.	e been received. e been received in Application No cuments have been received in this of this communication to file a reply IENT of this application.  itted. Note the attached EXAMINER es reason(s) why the oath or declara is to be submitted. Son's Patent Drawing Review ( PTO as Amendment / Comment or in the of .84(c)) should be written on the drawing he header according to 37 CFR 1.121 sit of BIOLOGICAL MATERIAL	national stage applical complying with the reconstruction of the front (not the (d)).	quirements IOTICE OF
Attachment(s)  1. ☐ Notice of References Cited (PTO-892)  2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)  3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/C Paper No./Mail Date  4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	5. Notice of Informal II 6. Interview Summary Paper No./Mail Da 7. Examiner's Amend 8. Examiner's Statem 9. Other	r (PTO-413), ate ment/Comment	

## Response to Amendment

Applicants' amendment filed by fax on March 11, 2005 has been entered on March 16, 2005.

Therefore claims 1,3-8,13-15,17,21 and 23 as amended by the amendment and claims 24-29 presently newly added are currently pending in the Application.

Claims 2,9-12,16,18-20 and 22 have been cancelled.

## Allowable Subject Matter

Claims 1,3-8,13-15,17, 21 and 23-29 are allowed.

The following is an examiner's statement of reasons for allowance:

The prior art taken either singularly or in combination fails to anticipate or fairly suggest the limitation of the dependent claims, in such manner that a rejection under 35 U.S.C. 102 or 103 would be proper. The applied prior art fails to teach a combination of all the claimed features as presented in independent claims, which include a semiconductor device as claimed in independent claims 1, 23 and 24 including the recitation of the width of the second /third trench sections is smaller than the width of the first trench section and the mesh pattern being formed by connecting trench sections having different widths, and further for claim 8 a semiconductor substrate a trench formed in le-substrate, at least one non-trench region surrounded by the trench an active region formed on the substrate over the trench for-driving current as a first diffusion region formed at a bottom of the trench In the active region'. And a second diffusion region formed in the non-trench region wherein current is flowable between the first diffusion region and me-second diffusion semiconductor element and further

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wherein the trench comprises a first trench section formed in the active region and a second trench section-intersecting the first trench section to form a mesh pattern surrounding the non-trench region wherein the first diffusion region is formed at the bottom of--ht e first trench section and wherein the semiconductor device is a trench lateral transistor composed of at least the semiconductor substrate, the first and second diffusion regions, the first diffusion region driving current as a transistor, a gate insulator film formed inside the trench, a first conductor formed inside the gate insulator film a second conductor formed inside the first conductor in the active region with an interlayer insulator film interposed there between and electrically connected to the first diffusion region, a first electrode penetrating through the interlayer insulator film electrically connected to the second diffusion region, and a second electrode penetrating through the interlayer insulator film to electrically connect to the second conductor.-Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Steven H. Rao whose telephone number is (571) 272-1718. The examiner can normally be reached on 8.00 to 5.00.

The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Steven H. Rao

Patent Examiner

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